



850nm Laser Diode

CHANGCHUN NEW INDUSTRIES
OPTOELECTRONICS TECH.CO., LTD.

■ Features

- Output Power: 50mW (CW)
- Efficient Quantum Well Structure
- Standard TO-18 Package



■ Absolute Maximum Ratings

Item	Symbol	Absolute Maximum Ratings	Unit
Optical Output Power	Po	50	mW
LD Reverse Voltage	Vr (LD)	3.5	V
Storage Temperature	Tstg	-40~85-	°C
Operating Case Temperature	Tc	-10~50	°C

■ Initial Electrical/Optical Characteristics

Item	Symbol	Typ.	Unit
Optical Output	Po	50	mW
Peak Wavelength*	λ_p	850±5	nm
Threshold Current	Ith	≤ 0.015	A
Operating Current	Iop	≤ 0.075	A
Slope Efficiency	η	≥ 0.8	W/A
Operating Voltage	Vop	≤ 1.8	V
Horizontal Beam Divergence	$\theta_{//}$	≤ 12	deg.
Vertical Beam Divergence	θ_{\perp}	≤ 30	deg.
Spectrum FWHM		<0.5	
Wavelength Temperature Coefficient		0.8	nm/°C
Polarization		TE	

* Measuring specifications.

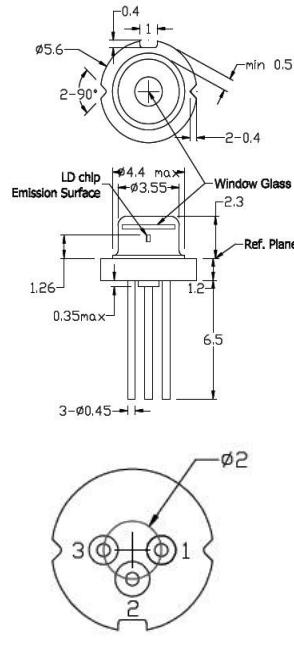
All figures in this specification are measured by CNI's method and may contain measurement deviations.

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The above specifications are for reference purpose only and subjected to change without prior notice.

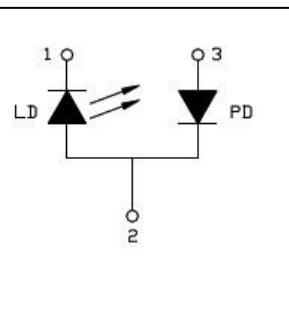
Outline Dimension

TO-18 Package



(Unit: mm)

Pin Connection



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◆ CONTACT

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